

# Tanmoy Das

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5972927/publications.pdf>

Version: 2024-02-01

24  
papers

1,039  
citations

758635

12  
h-index

676716

22  
g-index

26  
all docs

26  
docs citations

26  
times ranked

2315  
citing authors

| #  | ARTICLE  | IF   | CITATIONS |
|----|--|------|-----------|
| 1  | Gate-Controlled Rectifying Direction in PdSe <sub>2</sub> Lateral Heterojunction Diode. Advanced Electronic Materials, 2021, 7, 2100005.   | 2.6  | 5         |
| 2  | Polarity Control and Weak Fermi-Level Pinning in PdSe <sub>2</sub> Transistors. ACS Applied Materials & Interfaces, 2021, 13, 43480-43488.   | 4.0  | 9         |
| 3  | Doping-Free All PtSe <sub>2</sub> Transistor via Thickness-Modulated Phase Transition. ACS Applied Materials & Interfaces, 2021, 13, 1861-1871.  | 4.0  | 30        |
| 4  | Tunable Current Transport in PdSe <sub>2</sub> via Layer-by-Layer Thickness Modulation by Mild Plasma. Advanced Electronic Materials, 2020, 6, 2000008.  | 2.6  | 17        |
| 5  | Graphene-based flexible and wearable electronics. Journal of Semiconductors, 2018, 39, 011007.   | 2.0  | 76        |
| 6  | Surface-Functionalization-Mediated Direct Transfer of Molybdenum Disulfide for Large-Area Flexible Devices. Advanced Functional Materials, 2018, 28, 1706231.  | 7.8  | 66        |
| 7  | Development of electronic devices based on two-dimensional materials. FlatChem, 2017, 3, 43-63.  | 2.8  | 23        |
| 8  | Graphene-Based Flexible and Stretchable Electronics. Advanced Materials, 2016, 28, 4184-4202.  | 11.1 | 537       |
| 9  | Lithography-free plasma-induced patterned growth of MoS <sub>2</sub> and its heterojunction with graphene. Nanoscale, 2016, 8, 15181-15188.  | 2.8  | 68        |
| 10 | Highly Flexible Hybrid CMOS Inverter Based on Si Nanomembrane and Molybdenum Disulfide. Small, 2016, 12, 5720-5727.  | 5.2  | 46        |
| 11 | Flexible Electronics: Highly Flexible Hybrid CMOS Inverter Based on Si Nanomembrane and Molybdenum Disulfide (Small 41/2016). Small, 2016, 12, 5650-5650.  | 5.2  | 0         |
| 12 | Vertical field effect tunneling transistor based on graphene-ultrathin Si nanomembrane heterostructures. 2D Materials, 2015, 2, 044006.  | 2.0  | 12        |
| 13 | Interface Properties of Atomic Layer Deposited TiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> Films on In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP Substrates. ACS Applied Materials & Interfaces, 2014, 6, 3263-3274.  | 4.0  | 24        |
| 14 | Interface Properties of Mixed (TiO <sub>2</sub> ) <sub>x</sub> (Y <sub>2</sub> O <sub>3</sub> ) <sub>x</sub> and (Ta <sub>2</sub> O <sub>5</sub> ) <sub>x</sub> (Y <sub>2</sub> O <sub>3</sub> ) <sub>x</sub> (O <sub>2</sub> ) <sub>x</sub> Gate Dielectrics on Sulfur-Passivated GaAs. Journal of the Electrochemical Society, 2012, 159, H323-H328. | 1.3  | 7         |
| 15 | Atomic layer deposited (TiO <sub>2</sub> ) <sub>x</sub> (Al <sub>2</sub> O <sub>3</sub> ) <sub>1-x</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As gate stacks for III-V based metal-oxide-semiconductor field-effect transistor applications. Applied Physics Letters, 2012, 100, 062905.   | 1.5  | 30        |
| 16 | Degradation analysis and characterization of multifilamentary conduction patterns in high-field stressed atomic-layer-deposited TiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> nanolaminates on GaAs. Journal of Applied Physics, 2012, 112, 064113.   | 1.1  | 12        |
| 17 | Electrical properties and noise characterization of HfO <sub>2</sub> gate dielectrics on strained SiGe layers. Thin Solid Films, 2012, 522, 267-273.   | 0.8  | 3         |
| 18 | Studies on Lattice vibration, impurity and defects in MIS structures using Hf-based dielectrics on Si and SiGe substrates. , 2012, , .   |      | 0         |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 19 | Degradation and breakdown characteristics of Al/HfYOx/GaAs capacitors. Thin Solid Films, 2012, 520, 2956-2959.   | 0.8 | 1         |
| 20 | Effects of Ti incorporation on the interface properties and band alignment of HfTaOx thin films on sulfur passivated GaAs. Applied Physics Letters, 2011, 98, 022901.            | 1.5 | 19        |
| 21 | An extension of the Curie-von Schweidler law for the leakage current decay in MIS structures including progressive breakdown. Microelectronics Reliability, 2011, 51, 1535-1539. | 0.9 | 12        |
| 22 | Sputter-Deposited La2O3 on p-GaAs for Gate Dielectric Applications. Journal of the Electrochemical Society, 2011, 159, G15-G22.  | 1.3 | 28        |
| 23 | Surface Passivation of GaAs Substrates with SiO2 Deposited Using ALD. Electrochemical and Solid-State Letters, 2011, 14, G52.  | 2.2 | 10        |
| 24 | Thermal stability of HfOxNy gate dielectrics on p-GaAs substrates. Semiconductor Science and Technology, 2010, 25, 125009.   | 1.0 | 4         |